RoHS

COMPLIANT HALOGEN

FREE

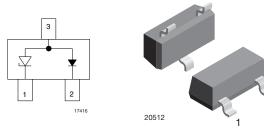
GREEN

(5-2008)



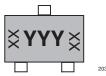
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Low Capacitance ESD Protection Diodes for High-Speed Data Interfaces



MARKING

(example only)



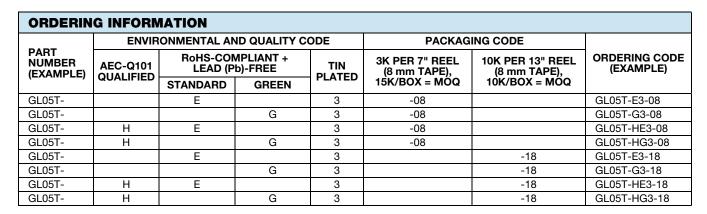
Bar = cathode marking YYY = type code (see table below) XX = date code

DESIGN SUPPORT TOOLS



FEATURES

- IEC 61000-4-5 (lightning) see I_{PPM} below
- ESD immunity acc. IEC 61000-4-2 ± 8 kV contact discharge ± 15 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- SOT-23 package
- · Low capacitance for high speed data lines, cellular handsets, USB port protection, LAN equipment, peripherals
- e3 Sn
- AEC-Q101 qualified available
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



PACK	PACKAGE DATA									
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS			
GL05T	GL05T SOT-23		Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GLOST	301-23	L06	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GL12T SOT-23		SOT-23	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GLIZI	301-23	L13	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GL15T	GL15T SOT-23		Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GLIST	301-23	L16	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GL24T SOT-23		L24	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			
GL241	301-23	L25	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C			

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ABSOLUTE MAXIMUM RATINGS GL05T								
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	8/20 μs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	25	Α			
Peak pulse power	8/20 µs waveform	Fiii 1-2 (βiii 3 ii.c.)	P _{PP}	300	W			
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV			
ESD Illillidility	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV			
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V _B	70	V			
Operating temperature Junction temperature		T _J	-55 to +150	°C				
Storage temperature			T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GL12T								
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	8/20 μs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	12	Α			
Peak pulse power	8/20 µs waveform	Pin 1-2 (pin 3 n.c.)	P _{PP}	300	W			
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV			
ESD Illillidility	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV			
Blocking voltage	$I_B = 1 \mu A$	Pin 2-1 or pin 2-3	V_{B}	70	V			
Operating temperature	Junction temperatu	Junction temperature		-55 to +150	°C			
Storage temperature			T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GL15T							
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	8/20 µs	Din 1 2 (nin 2 n a)	I _{PPM}	10	Α		
Peak pulse power	8/20 µs waveform	Pin 1-2 (pin 3 n.c.)	P _{PP}	300	W		
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV		
ESD Illillidility	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV		
Blocking voltage	$I_B = 1 \mu A$	Pin 2-1 or pin 2-3	V _B	70	V		
Operating temperature	Junction temperatu	re	T _J	-55 to +150	°C		
Storage temperature			T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GL24T								
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I _{PPM}	5	Α			
Peak pulse power	8/20 µs waveform	Fiii 1-2 (βiii 3 ii.c.)	P _{PP}	300	W			
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 8	kV			
ESD initiality	Air discharge acc. I	Air discharge acc. IEC 61000-4-2; 10 pulses		± 15	kV			
Blocking voltage	I _B = 1 μA	Pin 2-1 or pin 2-3	V _B	70	V			
Operating temperature Junction temperature			TJ	-55 to +150	°C			
Storage temperature	Storage temperature		T _{STG}	-55 to +150	°C			

The GLxxT contains an avalanche diode (pin 3-1) and a switching diode (pin 3-2). With pin 1 connected to the signal or data line and pin 2 connected to ground both diodes are in series (pin 3 remains unconnected). The big and robust avalanche diode, driven in reverse direction, provides the working range V_{RWM} of 5 V, 12 V, 15 V or 24 V. Due to its size the capacitance of the avalanche diode is in the range of typ. 260 pF (GL05T) and 65 pF (GL24T). The small switching diode in series has a low capacitance of just 2.5 pF (typ.). As both diodes are in series (with pin 3 not connected) the total capacitance of both diodes measured between pin 1 and 2 is as low as the capacitance of the switching diode.

Before the GLxxT can provide this low capacitance the big capacitance of the avalanche diode has to be charged up with the first signal or data pulses. This is usually no problem for digital signals like USB or other data ports.

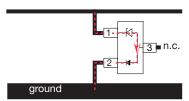
With the GLxxT a signal or data line can be protected against positive transients only. For negative transients another GLxxT can be used to provide a back path for the negative transients as well.



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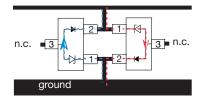
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Data line



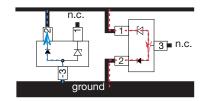
Uni Unidirectional clamping performance for positive transients only.

Data line



BiSy
Bidirectional and Symmetrical
clamping performance for positive
and negative transients.

Data line



BiAs
Bidirectional and Asymmetrical
clamping performance for positive
and negative transients.

ELECTRICAL CHARACTERISTICS GL05T (T_{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected **TEST CONDITIONS/REMARKS** SYMBOL **PARAMETER** MIN. TYP. MAX. UNIT Protection paths Number of lines which can be protected $N_{\text{cha}\underline{\text{nnel}}}$ lines Reverse stand-off voltage Max. reverse working voltage 5 ٧ V_{RWM} _ Reverse voltage at $I_R = 20 \mu A$ 5 ٧ V_{R} at $V_R = 5 \text{ V}$ 20 Reverse current μΑ I_R at $I_R = 1 \text{ mA}$ Reverse breakdown voltage 6.9 7.5 8.0 ٧ V_{BR} at $I_{PP} = 1 A$ _ _ 9.8 ٧ Reverse clamping voltage V_{C} at $I_{PP} = 5 A$ 11 ٧ at $V_R = 0 V$; f = 1 MHz2.5 5 Capacitance C_D pF

ELECTRICAL CHARACTERISTICS GL12T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V			
Reverse voltage	at I _R = 1 μA	V_R	12	-	-	V			
Reverse current	at V _R = 12 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.3	14.3	17.2	V			
Poverse elemping veltage	at I _{PP} = 1 A		-	-	19	V			
Reverse clamping voltage	at I _{PP} = 5 A	V _C	-	-	24	V			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	2.5	5	pF			

ELECTRICAL CHARACTERISTICS GL15T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15	V			
Reverse voltage	at I _R = 1 μA	V _R	15	-	-	V			
Reverse current	at V _R = 15 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.7	17.7	22	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	-	24	V			
neverse ciamping voltage	at I _{PP} = 5 A	¬ vc	-	-	33	V			
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	2.5	5	pF			



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ELECTRICAL CHARACTERISTICS GL24T (T _{amb} = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V			
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V			
Reverse current	at V _R = 24 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	26.7	28.2	33	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	-	43	V			
neverse ciamping voltage	at I _{PP} = 5 A	T vc	-	-	55	V			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	2.5	5	pF			

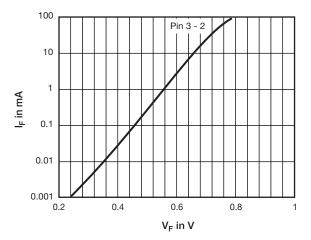


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

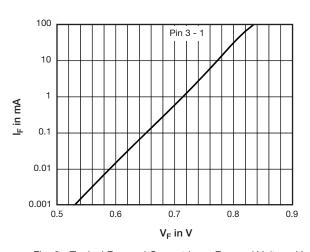


Fig. 2 - Typical Forward Current I_{F} vs. Forward Voltage V_{F}

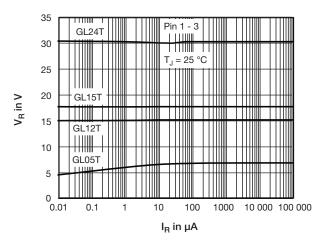
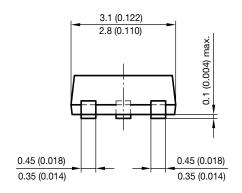


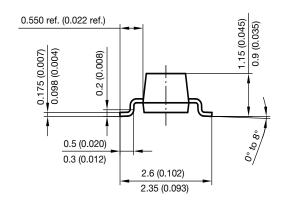
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

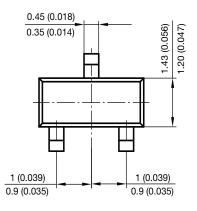


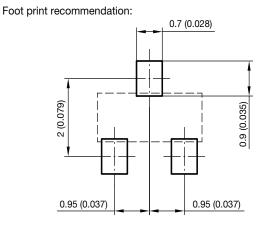
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PACKAGE DIMENSIONS in millimeters (inches): SOT-23



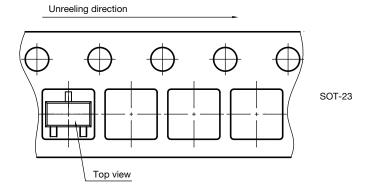






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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607



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